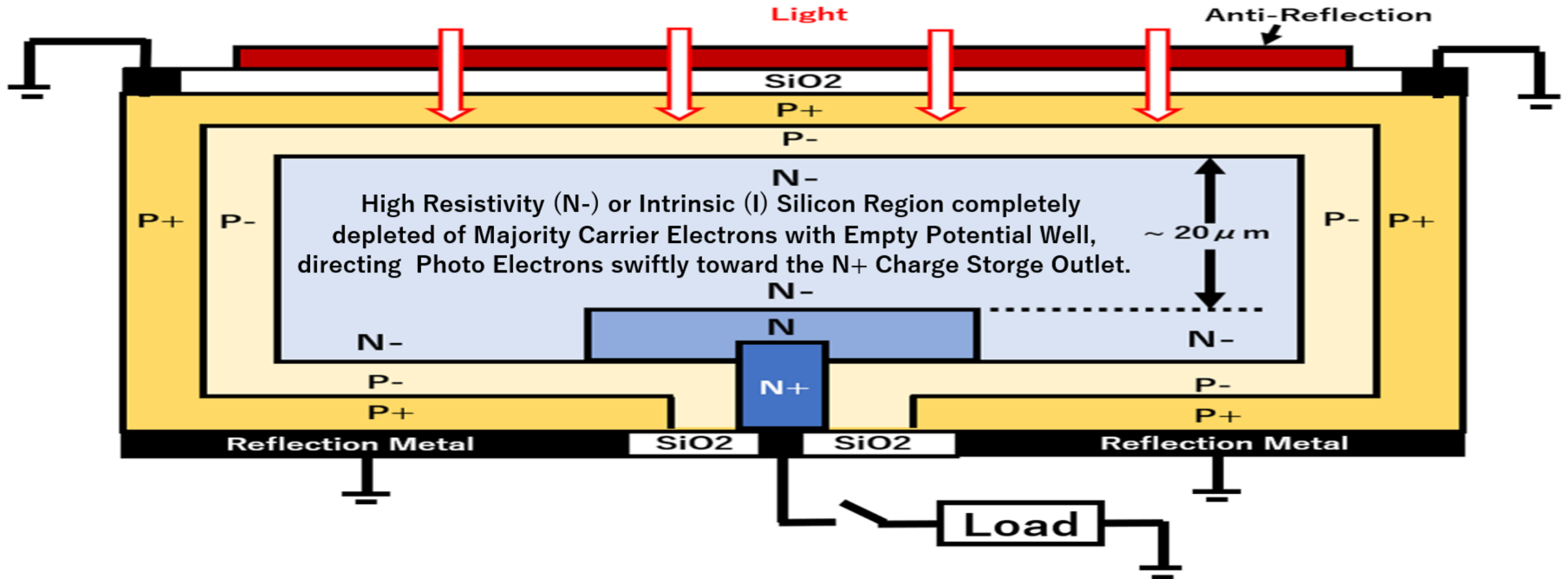


P+P-N-P-P+ Double Junction type Solar Cell invented and defined in JPA2020-131313 by Hagiwara(AIPS)

The surface P+P doping variation creates the Surface Barrier Drift Field, helping the separation of photo electron and hole pairs, enhancing the short-wave blue light sensitivity.



Backside Storage and Outlet NN+ region can be made small which does not contribute Photo Charge Separation.

See [ICECET2021_Paper61_html](#) and [ICECET2021_Paper75_html](#)